

Datasheet

V850ES/FE3-L

32-bit Single-Chip Microcontroller

Hardware

μPD70F3610(A)	μPD70F3611(A)	μPD70F3612(A)
μPD70F3610(A1)	μPD70F3611(A1)	μPD70F3612(A1)
μPD70F3610(A2)	μPD70F3611(A2)	μPD70F3612(A2)
μPD70F3613(A)	μPD70F3614(A)	
μPD70F3613(A1)	μPD70F3614(A1)	
μPD70F3613(A2)	μPD70F3614(A2)	

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V850ES/FE3-L



Notes for CMOS Devices

1. Precaution against ESD for semiconductors

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

2. Handling of unused input pins for CMOS

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

3. Status before initialization of MOS devices

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.



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1. Pin Group Information

1.1 Device package information

The V850ES/Fx3-L device series comprises several members. An overview with the pin and package information is given in the following table:

Series Member	# Pins	Device package information
μPD70F3610		
μPD70F3611		
μPD70F3612	64	FE3-L
μPD70F3613		
μPD70F3614		
μPD70F3615		
μPD70F3616		
μPD70F3617	80	FF3-L
μPD70F3618		
μPD70F3619		
μPD70F3620		
μPD70F3621	100	FG3-L
μPD70F3622		

This document describes the specification for the V850ES/FE3-L.

1.2 Pin Groups 1x: Pins supplied by EVDD

1B: (SHMT1)

- P04, P30-31, P34; P40, P91, P913-915 (FE3-L)
- P04, P30-31, P34; P38-39, P40, P91, P913-915 (FF3-L)
- P04, P30-31, P34; P36-39, P40, P91, P911, P913-915 (FG3-L)

1D: (SHMT3)

- P00-03, P05-P06, P32-33, P35, P41-42, P50-55, P90, P96-99 (FE3-L)
- P00-03, P05-P06, P32-33, P35, P41-42, P50-55, P90, P96-99 (FF3-L)
- P00-03, P05-P06, P10-11, P32-33, P35, P41-42, P50-55, P90, P92-910, P912 (FG3-L)

1.3 Pin Groups 2x: Pins supplied by EVDD

2A: (CMOS)

- PCM0-1 (FE3-L)
- PCM0-3, PCS0-1, PCT0-1, PCT4, PCT6 (FF3-L)

2D: (SHMT3)

- PDL0-7 (FE3-L)
- PDL0-11 (FF3-L)



1.4 Pin Groups 3x: Pins supplied by BVDD

3A: (CMOS)

- PCM0-3, PCS0-1, PCT0-1, PCT4, PCT6 (FG3-L)

3D: (SHMT3)

- PDL0-13 (FG3-L)

1.5 Pin Groups 4: Pins supplied by AVREF0

4: (CMOS)

- P70-79 (FE3-L)
- P70-711 (FF3-L)
- P70-715 (FG3-L)

1.6 Pin Groups 6: Pins supplied by EVDD

- RESET (SHMT2)
- IC, FLMD0

1.7 Pin Groups 7: Pins supplied by VRO

- X1, X2, XT1, XT2

V850ES/FE3-L



2. Electrical Specifications

This product has to be used only under the conditions of VDD=EVDD. Operation is not ensured at the time of using this product except this condition.

The operating ambient temperature of each quality grade is as follows:

(A)-Grade: $Ta = -40 \text{ to } +85^{\circ}\text{C}$ (A1)-Grade: $Ta = -40 \text{ to } +110^{\circ}\text{C}$ (A2)-Grade: $Ta = -40 \text{ to } +125^{\circ}\text{C}$

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (Ta=25°C)

		,						
Parameter	Symbol	Conditions			Rating	Unit		
	VDD	VDD=EV	DD,		-0.5 to +6.5			
	EVDD	VDD=EV	DD		-0.5 to +6.5			
Cumply valtage	AVREF0				-0.5 to +6.5	V		
Supply voltage	VSS	VSS=EVSS=	=AVSS		-0.5 to +0.5	v		
	EVSS	VSS=EVSS=	=AVSS		-0.5 to +0.5			
	AVSS	VSS=EVSS=	=AVSS		-0.5 to +0.5			
Input voltage	VI1	Pin Group 12	k, 2x, 6		-0.5 to EVDD+0.5 Note1	V		
	VI3	Pin Grou	p 7		-0.5 to VRO+0.5 Note1	V		
Analog input voltage	VIAN	Pin Grou	p 4		-0.5 to AVREF0+0.5 Note1	V		
				1 pin	-4			
		Din Croup 1v 2v		(A)	-50			
		Pin Group 1x, 2x	Total	(A1)	-20			
High level output current				(A2)	-20			
	IOH			1 pin	-4	mA		
		Pin Group 4	Total	(A) ^{Note2}	-20			
				(A1) ^{Note2}	-10]		
				(A2) ^{Note3}	-10			
			1 pin		4	1		
		Pin Group 1x, 2x		(A)	50			
		Fill Gloup 1x, 2x	Total	(A1)	20			
Low level				(A2)	20			
output current	IOL		1 pin		4	mA		
		Din Craun 4		(A) ^{Note2}	20			
		Pin Group 4	Total	(A1) ^{Note2}	10			
				(A2) ^{Note3}	10			
		Normal operating mod	le	(A)	-40 to +85			
Operating ambient temperature		Flash programming mo	de	(A)	-40 10 100			
	Та	Normal operating mode			-40 to +110	°C		
	la	Flash programming mo		(A1)	-40 10 1 110			
		Normal operating mod	le	(A2)	-40 to +125			
		Flash programming mo	de	(A2)	-40 to +120			
Storage temperature	Tstg				-40 to +125	°C		

Remarks: 1. The characteristics of the dual-function pins are the same as those of the port pins unless otherwise specified

Notes: 1. Be sure not to exceed the absolute maximum ratings (Max. value) of each supply voltage.

- 2. Excluding ADC IAREF0 current.
- 3. Including ADC IAREF0 current.



2.2 Capacities

(Ta = 25°C, VDD = EVDD = AVREF0 = VSS = EVSS = AVSS = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input/output capacitance	CIO	f=1MHz, Not measured pins is 0V.			10	pF

2.3 Operating condition

 $(Ta = -40 \text{ to } +85^{\circ}\text{C for (A)-Grade, } Ta = -40 \text{ to } +110^{\circ}\text{C for (A1)-Grade, } Ta = -40 \text{ to } +125^{\circ}\text{C for (A2)-Grade, } C=4.7 \text{uF, VDD} = \text{EVDD} = 3.3 \text{ to } 5.5\text{V, AVREF0} = 3.3 \text{ to } 5.5\text{V, VSS} = \text{EVSS} = \text{AVSS} = \text{OV})$

Internal System clock frequency (f_{VBCLK})	Supply voltage	Operating Condition
	3.5V≤VDD≤5.5V ^{Note1}	Operation of functions is enabled
4.0≤f _{xx} ≤20MHz Note1	3.3V≤VDD<3.5V	The following functions are operable: CPU Flash (including programming RAM IO Buffer Port WT UDT INT CLM POC LVI
	3.3V≤AVRF0≤5.5V	 A/D Converter stop ADC for AVREF0 < 4.0V (ADA0CE bit =0) Refer to chapter '2.8 A/D Converter' for details.
32kHz≤f _{XT} ≤35kHz (Crystal)	3.3V≤VDD<5.5V	
12.5kHz≤f _{XT} ≤27.5kHz ^{Note2} (RC)	Note1	-
f _{RL} (240kHz Internal-OSC)	3.3V≤VDD<5.5V ^{Note1}	-

Notes: 1. VDD = EVDD

2. RC Oscillation frequency is min. 25kHz max. 55kHz. This clock is divided by 2 internally.



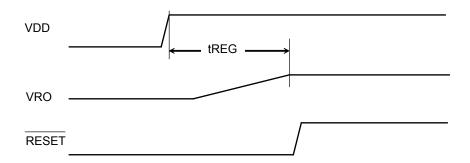
2.4 Voltage Regulator Characteristics

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7 μ F, VDD = EVDD, VSS = EVSS = AVSS = 0V))

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage	VDD		3.5		5.5	V
Input voltage	کان	Limited function see '2.3 Operating condition'	3.3			V
Output voltage	VRO			2.5		V
Output voltage	t _{REG} Note	After VDD reaches voltage range min. 3.3V			1	ms
stabilization time	¹ REG	To connect C=4.7uF on REGC terminal			'	1115

Note: In case of non-POC device, be sure to start VDD in the state of RESET=VSS=0V.

For POC devices there is no need to control external RESET terminal. For decives with POC function the internal RESET signal will automatically controlled until VRO is stable.



2.5 Clock Generator Circuit

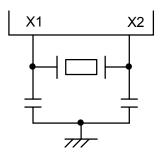
2.5.1 Main System Clock Oscillation Circuit Characteristics

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V)

Resonator	Recommended Circuit	Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Crystal /	Defeate favore heles	Oscillator fre- quency (fx) ^{Note1}		4		16	MHz
Ceramic resona- tor	Refer to figure below	Oscillation stabili-	After STOP mode	54 ^{Note4}	Note3		μs
tor		zation time Note2	After IDLE2 mode	54 ^{Note4}	Note3		μs

Notes: 1. Indicates only oscillation circuit characteristics. Refer to '2.7 AC Characteristics' for CPU operation clock.

- 2. Time required to stabilize oscillation after VDD reaches oscillator voltage range MIN. 3.3V
- **3.** Depends on the setting of the oscillation stabilization time select register (OSTS)
- **4.** Minimum time required to stabilize flash. Time has to be secured by setting the oscillation stabilization time select register (OSTS)





XT2

2.5.2 Sub System Clock Oscillation Circuit Characteristics

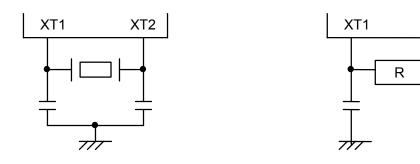
(Ta = -40 to +85°C, C=4.7uF, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V)

`		,	•		,		
Resonator	Recommended Circuit	Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Crystal	Refer to Figure 1	Oscillator fre- quency (fxt) ^{Note1}		32	32.768	35	kHz
resonator	Refer to Figure 1	Oscillation stabiliza- tion time Note2				10	s

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD=EVDD=3.3 to 5.5V, AVREF0=3.3 to 5.5V, VSS=EVSS=AVSS=0V)

Resonator	Recommended Circuit	Parameter	Conditions	MIN.	TYP.	MAX.	Unit
RC	Refer to Figure 2	Oscillator frequency ^{Note1,4}	R=390K Ω ±5% Note3, C=47pF±10% Note3	25	40	55	kHz
resonator	Refer to Figure 2	Oscillation stabiliza- tion time Note2				100	μs

- **Notes: 1.** Indicates only oscillation circuit characteristics. Refer to "AC Characteristic" for cpu operation clock.
 - 2. Time required to stabilize oscillation after VDD reaches oscillator voltage range min. 3.3V
 - 3. In order to avoid the influence of wiring capacity, shorten wiring as much as possible.
 - **4.** RC Oscillation frequency is typ. 40kHz. This clock is divided (1/2) internally. In case of RC Oscillator, internal system clock frequency (fxt) is min. 12.5kHz, typ. 20kHz, max. 27.5kHz.



2.5.3 Internal-OSC Characteristics

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output	f _{RL}	240kHz Internal-OSC	204	240	276	kHz
frequency	f _{RH}	8MHz Internal-OSC	7.2	8.0	8.8	MHz
Oscillation		240kHz Internal-OSC		10	36	μs
stabilization time		8MHz Internal-OSC	51	92	256	μs



2.5.4 PLL Characteristics

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7 μ F, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input fraguancy	fx		4		16	MHz
Input frequency	f_PLLI	Note1	3		6	MHz
Output frequency	fxx		10		20	MHz
Lock time	tPLL	After VDD reaches voltage range min. 3.3V			800	μs
Output period jitter Note2	tpj	Peak to peak			2.0	ns

Notes: 1. The input of the PLL (f_{PLLI}) can be set to f_X , $f_X/2$, or $f_X/4$. The divider is set through an option byte in the code flash memory.

2. Not tested in production.



2.6 DC Characteristics

2.6.1 Input/Output Level

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V)

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
	VIH1		roup 1B	0.7·EVDD		EVDD	V
	\/II.IO	Pin G	roup 1D	0.8·EVDD		EVDD	V
High level	VIH2	Pin G	roup 2D	0.8·EVDD		EVDD	V
input voltage	VIH3	Pin G	roup 2A	0.7·EVDD		EVDD	V
	VIH4	Pin (Group 4	0.7·AVREF0		AVREF0	V
	VIH5	Pin (Group 6	0.8·EVDD		EVDD	V
	VIL1	Pin G	roup 1B	EVSS		0.3·EVDD	V
	VIII O	Pin G	roup 1D	EVSS		0.4·EVDD	V
Low level	VIL2	Pin G	roup 2D	EVSS		0.4·EVDD	V
input voltage	VIL3	Pin G	roup 2A	EVSS		0.3·EVDD	V
	VIL4	Pin (Group 4	AVSS		0.3·AVREF0	V
	VIL5	Pin (Group 6	EVSS		0.2·EVDD	V
	VHYS1	Pin Group 1B	Center point at 0.5·EVDD Note3		0.267·EVDD - 0.51V		V
Input byotoroois	VHYS2	Pin Group 1D	Center point at 0.6·EVDD Note3		0.192·EVDD - 0.31V		V
Input hysteresis	VIII 32	Pin Group 2D	Center point at 0.6·EVDD Note3		0.192·EVDD - 0.31V		V
	VHYS5	Pin Group 6	Center point at 0.5·EVDD Note3		0.535·EVDD - 0.9V		٧
	VOH1	Pin Group	IOH=-1.0mA	EVDD-1.0		EVDD	V
High level output voltage	VOIII	1x, 2x	IOH=-100μA	EVDD-0.5		EVDD	V
Note2	VOH3	Pin Group 4	IOH=-1.0mA	AVREF0-1.0		AVREF0	V
		·	IOH=-100μA	AVREF0-0.5		AVREF0	V
Low level output	VOL1	Pin Group 1x, 2x	IOL=1.0mA	0		0.4	V
voltage ^{Note2}	VOL 2	P914, 915	IOL=3.0mA IOL=1.0mA	0		0.4	V
Software pull-up	VOL3	Pin Group 4		_		0.4	
resistor	R1	V	I=0V	10	30	100	kΩ
Software Note1 pull-down resistor	R2	VI=	=VDD	10	30	100	kΩ

Remark: The characteristics of the dual-function pins are the same as those of the port pins unless otherwise specified.

Notes: 1. DRST terminal only. (Control register is OCDM)

- 2. Total IOH/IOL for each power supply line (EVDD and AVREF0).
 - (A-Grade) :max 20mA/-20mA
 - (A1-/A2-Grade): max. 10mA/-10mA

AVREF0 IOH/IOL current is excluding ADC0 current IAREF0.

3. Typical value. Not tested and guaranteed



2.6.2 PIN leakage current

(C=4.7uF, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V)

(O 4.7 al , VDD LVDD	0.0 to 0.01,	AVILLO 0.0 (,	0 710		,			
Parameter	Symbol	Co	nditions	MIN.	TYP.		MAX.		Unit
Farameter	Symbol	Co	HUILIONS	IVIIIN.	IIF.	(A)	(A1)	(A2)	Offic
High level input leak-	ILIH1	VI=VDD	Analog pins			0.2	0.4	0.5	
age current	ILINI	VI=VDD	Other pins Note1			0.5	0.8	1.0	
Low level input	ILIL1	VI=0V	Analog pins			-0.2	-0.4	-0.5	
leakage current	ILILI	V1-0V	Other pins Note1			-0.5	-0.8	-1.0	μA
High level output	ILOH1	VO=VDD	Analog pins			0.2	0.4	0.5	μΑ
leakage current	ILOHI	VO=VDD	Other pins			0.5	0.8	1.0	
Low level output	ILOL1	VO=0V	Analog pins			-0.2	-0.4	-0.5	
leakage current	ILOLI	VO-0V	Other pins			-0.5	-0.8	-1.0	

Notes: 1. The input leakage current of FLMD0 is as follows:

High level input leakage current :

- (A)-Grade 2.0μA
- (A1)-Grade $4.0\mu A$
- (A2)-Grade 5.0μA

Low level input leakage current:

- (A)-Grade -2.0μA
- (A1)-Grade -4.0μA
- (A2)-Grade $5.0\mu A$

2.6.3 Power supply current

2.6.3.1 FE3-L µPD70F3610, µPD70F3611, µPD70F3612, µPD70F3613, µPD70F3614

(a) Absolute values

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7 μ F, VDD = EVDD = 3.3 to 5.5 ν 4, AVREF0 = 3.3 to 5.5 ν 4, VSS = EVSS = AVSS = 0 ν Note¹)

_																								
	<u>;</u>	OIII	Δm	[•	ШA		mA		•	MA		HA	•	HA	V	HA		mA			E E	V	HA
1	MAX.	(A) (A1) (A2)	PC	† N		35		19		· ·	78	C	32						1					
	Δ		16	2	į	25		12		0	70	Č	77	,	<u>.</u>	5	7		=			<u> </u>	5	1.7
, AO-			$f_{xx}=10MHz$	f _x =5MHz	f _{xx} =20MHz	f _x =10MHz	f _{xx} =8MHz	8MHz Internal-	OSC Note3	f _{xx} =16MHz	f _x =16MHz	f _{xx} =20MHz	f _x =10MHz	f _{xx} =10MHz	f _x =5MHz	f _{xx} =20MHz	f _x =10MHz	f _{xx} =8MHz	8MHz Internal-	OSC Note3	f _{xx} =16MHz	f _x =16MHz	f _{xx} =20MHz	f _v =10MHz
C-4.7 LT, VDD - EVDD - 5.3 IO 5.3V, AVRETO - 5.3 IO 5.3V, V33 - EV33 - AV33 - UV	Condition	יומונוסוו		PLL: ON 16MHz <f<sub>xx<20MHz PLL: OFF 4MHz<f<sub>xx<16MHz</f<sub></f<sub>									10MHz <f<sub>xx<20MHz</f<sub>		PLL: ON	16MHz <f<sub>xx<20MHz</f<sub>				PLL: OFF	4IVIII ZXX		PLL: ON	10MHz≤f _{xx} <20MHz
KELU - 5.5 IO 5.5V,	Č	00										Peripheral: f _{xx} /2	PRSI option: 1				- Joseph	PDSI ontion: 0					Peripheral: f _{xx} /2	PRSI option: 1
7 - 5.5 to 5.5V, AV			All peripherals running																All peripherals	naddois				
10 - EVDI	Cympol	oy III											2	וחחו										
0-4./ur, vr	Mode												Operating	mode	7000									



±.	5	{	<u>{</u>		E E		mA			¥ E	{	<u>{</u>	{	<u> </u>		¥ E		МA			H A	•	E E
MAX.	(A) (A1) (A2)	7 U	<u>n</u>	L	25		7		7	<u>o</u>	7	- N											
L C Y	11.	7	2	7	<u> </u>		7		7.0	7	7.7	<u>†</u>	7	,	7.0	7		2			ი	,	E
		$f_{xx}=10MHz$	f _x =5MHz	f _{xx} =20MHz	$f_x=10MHz$	f _{xx} =8MHz	8MHz Internal-	OSC Note3	f _{xx} =16MHz	f _x =16MHz	f _{xx} =20MHz	$f_x=10MHz$	f _{xx} =10MHz	f _x =5MHz	f _{xx} =20MHz	f _x =10MHz	f _{xx} =8MHz	8MHz Internal-	OSC Note3	f _{xx} =16MHz	f _x =16MHz	f _{xx} =20MHz	$f_x=10MHz$
;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;	COITUILIOII	PLL: ON 16MHZ≤f _{xx} <20MHz PLL: OFF 4MHZ≤f _{xx} <16MHz PLL: ON 10MHz≤f _{xx} <20MHz											PLL: ON	16MHz <f<sub>xx<20MHz</f<sub>			L (PLL: OFF	TIMIN IZXI ZX		PLL: ON	10MHz≤f _{xx} <20MHz	
Č	Ō	Peripheral: f _{xx} PRSI option: 0									Peripheral: f _{xx} /2	PRSI option: 1					Periprieral: I _{xx}	TRSI OPHOLI: 0				Peripheral: f _{xx} /2	PRSI option: 1
		All peripherals running															-1	All peripherals	stopped				
loden, O	Symbol											נכם	2001										
0000	Mode											HALT	mode										



:	- Unit	шА	mA	шĄ	mA	mA	mA	mA	mA	шĄ	МA	mA	mA	Υd	Αμ	Αď	Αμ	Αμ	М	Αď	ηЧ	hΑ	<
	(A2)	2.8	3.7	4.2	2.9					7.	7:	1.7	1.0		850	1450		029	930	230	545	535	ı
MAX.	(A1)	2.5	3.4	3.9	2.6		1			6.0	1.2	4.1	0.7		009	1200		420	380	280	295	285	
	(A)	2.2	3.1	3.6	2.3					0.7	1.0	1.2	0.5	400	400	1000	190	220	180	80	92	82	007
ĺ	ΤΥΡ.	4.1	2.0	2.4	1.5	1.2	4.1	1.6	1.1	0.4	0.7	0.8	0.2	80	80	220	20	40	25	2.2	15.5	10.5	107
		f _{xx} =5MHz f _x =5MHz	$f_{xx}=12MHz$ $f_x=12MHz$	f _{xx} =16MHz f _x =16MHz	ernal-OSCNote3	f _{xx} =5MHz f _x =5MHz	f_{xx} =12MHz f_x =12MHz	f _{xx} =16MHz f _x =16MHz	ernal-OSCNote3	f _{xx} =5MHz f _x =5MHz	f_{xx} =12MHz f_x =12MHz	f _{xx} =16MHz f _x =16MHz				<u> </u>				do	king	do	
	Condition		PLL: OFF 4MHz≤f _{xx} ≤16MHz	NOIS	fxx=8MHz, 8MHz Internal-OSCNote3		PLL: OFF $f_x=12MHz$ $4MHz \le f_{xx} \le 16MHz$ $hote 7$ $f_x=12MHz$ $f_x=12MHz$ $f_x=16MHz$ $f_x=16MHz$ $f_x=16MHz$ $f_x=16MHz$				ZH		fxx=8MHz, 8MHz Internal-OSC Note3	Crystal resonator (fxt = 32,768kHz)	RC resonator (fxt=20kHz) Note6	240 kHz Internal-OSC (SubOSC stopped)	Crystal resonator (fxt = 32,768kHz)	RC resonator (fxt=20kHz) Note6	240kHz Internal-OSC (SubOSC stopped)	240kHz Internal-OSC stop	240kHz Internal-OSC working	240kHz Internal-OSC stop	
(රි		Peripheral (TAA, UARTD) run-	Ď.			peripherals stopped				PLL: OFF 4MHz≤f _{xx} ≤16MHz _{Note7}		fxx=8MHz, 8MH	Crystal resonate	RC resonator	240 kHz Internal-O	Crystal resonate	RC resonator	240kHz Internal-O	24(240k	24(
			Peripheral (T ^A	_			All peripherals														r OC stop	Jugary Cod	25×))
	Symbol				נטט	SOO					IDD4				IDD5			9001			7001	<u>ה</u>	
	Mode		IDLE1 mode							IDLE2	D D		SUB	operating	mode ^{Note5}	SubIDLE	mode	Note3,5	() 	SIOP	Note3 4	1,0000	

(b) Calculation formulas (Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V^{Note1})

1	ן, יין בין	- EVDD	- 5.5 to 5.54, Av	NEL 0 = 3.3 tO 3.34,	C-4./ur, VD - EVDD - 5.3 (0 3.3V, AVNETO - 5.3 (0 3.3V, V33 - EV33 - AV33 - UV	, ,		0 1 14		
Σ	Mode	Symbol		Condition		TVD Note8		MAX. Note8		Unit
2	2	Ogili (o				<u>.</u>	(A)	(A1)	(A2)	
				Peripheral: f _{xx}	PLL: ON 16MHz≤f _{xx} <20MHz	0.93·f _{xx} +6.3		1.12·f _{xx} +12.6		mA
			All peripherals running	PRSI option: 0	PLL: OFF 4MHZ <f<sub>xx<16MHz</f<sub>	0.93·f _{xx} +4.7		1.12.f _{xx} +9.7		mA
) Jpe	Operating	5		Peripheral: f _{xx} /2 PRSI option: 1	PLL: ON 10MHz <f<sub>xx<20MHz</f<sub>	0.85·f _{xx} +5.2		1.03·f _{xx} +11.3		mA
ΕŻ	Mode Note2	_ 		Peripheral: ff _{xx} -	PLL: ON 16MHz≤f _{xx} <20MHz	0.78·f _{xx} +5.4				mA
			All peripherals stopped	PRSI option: 0	PLL: OFF 4MHZ <f<sub>xx<16MHz</f<sub>	0.80·f _{xx} +4.9		ı		mA
				Peripheral: f _{xx} /2 PRSI option: 1	PLL: ON 10MHz≤f _{xx} <20MHz	0.76·f _{xx} +5.4				mA
				Peripheral: ff _{xx} -	PLL: ON 16MHz≤f _{xx} <20MHz	0.70·f _{xx} +3.0		0.97*f _{xx} +5.2		mA
			All peripherals running	PRSI option: 0	PLL: OFF 4MHZ <f<sub>xx<16MHz</f<sub>	0.65·f _{xx} +1.9		0.90*f _{xx} +3.6		mA
Ĭ	HALT			Peripheral: f _{xx} /2 PRSI option: 1	PLL: ON 10MHz≤f _{xx} <20MHz	0.54·f _{xx} +2.8		0.63*f _{xx} +8.60		mA
Ε	mode	וממן ממן		Peripheral: f _{xx}	PLL: ON 16MHz≤f _{xx} <20MHz	0.46·f _{xx} +2.8				mA
			All peripherals stopped	PRSI option: 0	PLL: OFF 4MHZ <f<sub>xx<16MHz</f<sub>	0.44·f _{xx} +1.6		ı		mA
				Peripheral: f _{xx} /2 PRSI option: 1	PLL: ON 10MHz≤f _{xx} <20MHz	0.46·f _{xx} +1.8				mA
_ ⊑	IDLE1 mode	EQQI	Peripheral (TA	Peripheral (TAA, UARTD) run- ning	PLL: OFF 4MHZ≤f _{xx} ≤16MHz	0.092.f _{xx} +0.90	0.128·f _{xx} + 1.52	0.128·f _{xx} + 1.82	0.128·f _{xx} +2.12	mA
			All periphe	All peripherals stopped		0.035·f _{xx} +1.01		ı		mA
<u>□</u> E	IDLE2 mode	IDD4	,	PLL: OFF 4MHz ≤f _{xx} ≤16MHz Note7	, Note7	0.037·f _{xx} +0.21	0.049·f _{xx} + 0.43	0.049·f _{xx} + 0.63	0.049·f _{xx} + 0.88	шА

V850ES/FE3-L

Notes: 1. VDD and EVDD total current. (Ports are stopped).

AVREF0 current, port buffer current (including a current flowing in the on-chip pull-up/pull-down resistor) are not included.

2. The code flash is in read mode.

When the device is in programming mode (Self-programming mode) the current value (MAX. value) adds by the following value:

Self-programming mode:

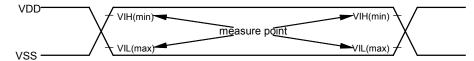
+ In case of PLL OFF: 7-(0.33*fxx+0.1) [mA] + In case of PLL ON: 7-(0.18*fxx+3.0) [mA]

- 3. Main OSC is stopped.
- 4. Do not use SubOSC.
- 5. POC is working. 240kHz Internal-OSC is working. 8MHz Internal-OSC is stopped.
- **6.** RC Oscillation frequency is typ.40kHz. This clock is divided by 1/2 internally.
- 7. 8MHz Internal-OSC is stopped
- **8.** The formulas are for reference only. Not all possible values for f_{XX} are tested in the outgoing device inspection.

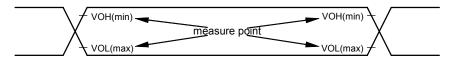


2.7 AC Characteristics

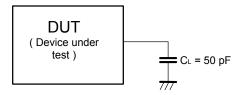
AC test Input measurement points (VDD, AVREF0, EVDD)



AC test output measurement points



Load conditions



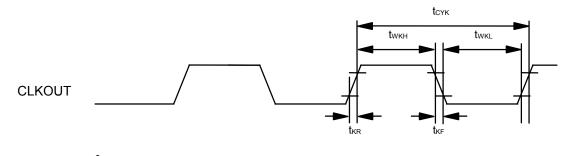
Caution: If the load capacitance exceeds 50pF due to the circuit configuration, reduce the load capacitance of the device to 50pF or less by inserting a buffer or by some other means.

2.7.1 CLKOUT Output Timing

 $(Ta = -40 \text{ to } +85^{\circ}\text{C for (A)-Grade}, Ta = -40 \text{ to } +110^{\circ}\text{C for (A1)-Grade}, Ta = -40 \text{ to } +125^{\circ}\text{C for (A2)-Grade}, VDD = EVDD = 3.5 \text{ to } 5.5\text{V}, AVREF0 = 3.5 \text{ to } 5.5\text{V}, VSS = EVSS = AVSS = 0V, CL=50pF)}$

Parameter	Symbol	Conditions	MIN.	MAX.	Unit	
Output cycle	tCYK		50ns	80µs		
Lligh lovel width	tWKH	VDD = EVDD = 4.0V ~ 5.5V	tCYK/2-13		no	
High level width	LVVKIT	VDD = EVDD = 3.5V ~ 5.5V	tCYK/2-15		ns	
Low level width	tWKL	VDD = EVDD = 4.0V ~ 5.5V	tCYK/2-13		no	
Low level width	IVVKL	VDD = EVDD = 3.5V ~ 5.5V	tCYK/2-15		ns	
Rise time	tKR	VDD = EVDD = 4.0V ~ 5.5V		13	no	
Rise time	INK	VDD = EVDD = 3.5V ~ 5.5V		15	ns	
Fall time	+I/E	VDD = EVDD = 4.0V ~ 5.5V		13	no	
raii liine	ie tKF	me tKF	VDD = EVDD = 3.5V ~ 5.5V		15	ns

CLKOUT output timing





2.7.2 RESET, Interrupt, ADTRG Timing

 $(Ta = -40 \text{ to } +85^{\circ}\text{C for (A)-Grade}, Ta = -40 \text{ to } +110^{\circ}\text{C for (A1)-Grade}, Ta = -40 \text{ to } +125^{\circ}\text{C for (A2)-Grade}, VDD = EVDD = 3.3 \text{ to } 5.5\text{V}, AVREF0 = 3.3 \text{ to } 5.5\text{V}, VSS = EVSS = AVSS = 0V, CL=50pF)}$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
_RESET input low level width	tWRSL	analog filter	250			ns
NMI input high level width	tWNIH	analog filter	250			ns
NMI input low level width	tWNIL	analog filter	250			ns
INTPn ^{Note1} input high level width	tWITH	analog filter ,n=0-8	250			ns
INTERPOSE Input high level width	LVVIIII	digital filter ,n=3	Note2			ns
INTPn Note1 input low level width	tWITL	analog filter ,n=0-8	250			ns
invirii input low level width	LVVIIL	digital filter ,n=3	Note2			ns

Notes: 1. ADTRG is same spec (P03/INTP0/ADTRG). DRST is same spec (P05/INTP2/DRST)

2. 2Tsamp+20 or 3Tsamp+20 ("Tsamp" is Noise reject sampling clock (NF macro))

Remarks: 1. The above minimum values show pulse widths that are surely detected as an effective edge. An effective may also be detected even if the input pulse width is less than the above minimum specification.

2. RESET, NMI, INTPn, ADTRG and DRST have analog noise filter. The typical filter time is typ=60ns.

2.7.3 Key Return Timing

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
KRn input high level width	tWKRH	analog filter ,n=0-7	250			ns
KRn input low level width	tWKRL	analog filter ,n=0-7	250			ns

Remarks: 1. The above minimum values show pulse widths that are surely detected as an effective edge. An effective may also be detected even if the input pulse width is less than the above minimum specification.

2. KRn inputs have analog noise filter. The typical filter time is typ=60ns.

2.7.4 Timer Timing

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, VDD = EVDD = 3.5 to 5.5V, AVREF0 = 3.5 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

100 2100 0.010	J. J		oo oo, o= oop.,				
Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
TI input high level width	tTIH	TIAA00-01,10-11,20-21,30-31,4	.0-41 Note1	250			ns
TI input low level width	tTIL	TIAA00-01,10-11,20-21,30-31,4	.0-41 Note1	250			ns
TO output cycle	tTCYK	TIAA00-01,10-11,20-21,30-31,	40-41 Note1			10	MHz

Notes: 1. Except for the external trigger and external event function.

Remarks: 1. The above minimum values show pulse widths that are surely detected as an effective edge. An effective may also be detected even if the input pulse width is less than the above minimum specification.

2. TIAAn inputs have analog noise filter. The typical filter time is typ=60ns.



2.7.5 CSI Timing

(a) Master mode

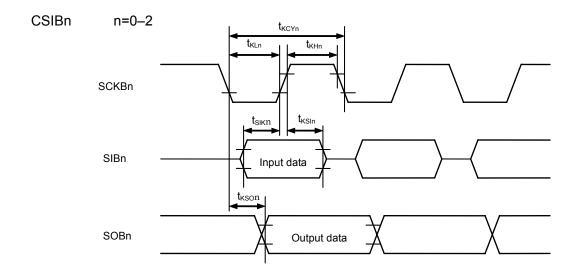
(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, VDD = EVDD = 3.5 to 5.5V, AVREF0 = 3.5 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCKBn cycle time	tKCY1		125		ns
SCKBn high level width	tKH1		tKCY1/2-15		ns
SCKBn low level width	tKL1		tKCY1/2-15		ns
SIBn setup time (to SCKBn)	tSIK1		30		ns
SIBn hold time (from SCKBn)	tKSI1		25		ns
Delay time from SCKBn to SOBn	tKSO1			25	ns

(b) Slave mode

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, VDD = EVDD = 3.5 to 5.5V, AVREF0 = 3.5 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCKBn cycle time	tKCY1		200		ns
SCKBn high level width	tKH1		90		ns
SCKBn low level width	tKL1		90		ns
SIBn setup time (to SCKBn)	tSIK1		50		ns
SIBn hold time (from SCKBn)	tKSI1		50		ns
Delay time from SCKBn to SOBn	tKSO1			50	ns



2.7.6 UART Timing

 $(Ta = -40 \text{ to } +85^{\circ}\text{C for (A)-Grade, } Ta = -40 \text{ to } +110^{\circ}\text{C for (A1)-Grade, } Ta = -40 \text{ to } +125^{\circ}\text{C for (A2)-Grade, } VDD = \text{EVDD} = 3.5 \text{ to } 5.5\text{V, AVREF0} = 3.5 \text{ to } 5.5\text{V, VSS} = \text{EVSS} = \text{AVSS} = 0\text{V, CL} = 50\text{pF})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate					1.5	Mbps
ASCK0 frequency					10	MHz



2.7.7 IIC Timing

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, VDD = EVDD = 3.5 to 5.5V, AVREF0 = 3.5 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

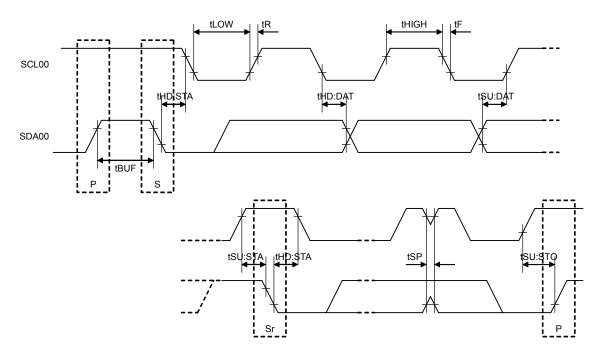
	December 2	•	Normal	mode	High-spee	d mode	1.1
	Parameter	Symbol	min.	max.	min.	max.	Unit
SCL00 clock	frequency	fCLK	0	100	0	400	kHz
Bus-free time tions)	(between stop/start condi-	tBUF	4.7		1.3		μs
Hold time ^{Note}	1	tHD:STA	4.0		0.6		μs
SCL00 clock	low-level width	tLOW	4.7		1.3		μs
SCL00 clock	high-level width	tHIGH	4.0		0.6		μs
Setup time for	r start/restart conditions	tSU:STA	4.7		0.6		μs
Data hold	CBUS compatible master	+UD.DAT	5.0				μs
time	IIC mode	tHD:DAT	0 ^{Note2}		0 ^{Note2}	0.9 ^{Note3}	μs
Data setup tin	ne	tSU:DAT	250		100 ^{Note4}		ns
SDA00 and S	CL00 signal rise time	tR		1000	20+0.1Cb	300	ns
SDA00 and S	CL00 signal fall time	tF		300	20+0.1Cb	300	ns
Stop condition	n setup time	tSU:STO	4.0		0.6		μs
Pilse width wi input filter	th spike supporessed by	tSP			0	50	ns
Capacitance I	oad of each bus line	Cb		400		400	pF

Notes: 1. At the start condition, the first clock pulse is generated after the hold time

- 2. The system requires a minimum of 300ns hold time Internally for the SDA signal (at VIHmin. of SCL00 signal)
 - In order to occupy the undefined area at the falling edge of SCL00.
- **3.** If the system does not extend the SCL00 signal low hold time (tlow), only the maximum data hold time (tHD:DAT) needs to be satisfied.
- **4.** The high-speed-mode IIC bus can be used In a normal-mode IIC bus system. In this case, set the high-speed-mode IIC bus so that It meets the following conditions.
 - If the system does not extend the SCL00 signal's low state hold time: SU:DAT?250ns
 - If the system extends the SCL00 signal's low state hold time: Transmit the following data bit to the SDA00 line prior to releasing the SCL00 line (tRmax.+tSU:DAT=1000+250=1250ns: Normal mode IIC bus specification).
- **5.** Cb: Total capacitance of one bus line (unit: pF)



IIC bus interface timing



Remark: P: Stop condition S: Start condition

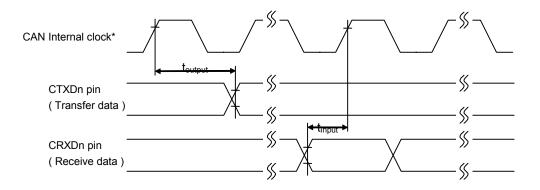
S: Start condition Sr: Restart condition



2.7.8 CAN Timing

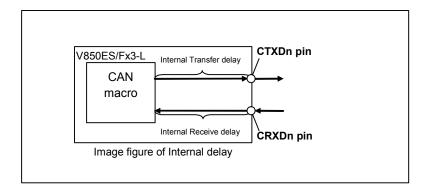
(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, VDD = EVDD = 3.5 to 5.5V, AVREF0 = 3.5 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate					1	Mbps
Internal delay time					100	ns



 $Internal\ delay\ time\ (tNODE) = Internal\ Transfer\ Delay(t_{output}) + Internal\ Receive\ Delay(t_{input})$

*) CAN Internal clock (f_{CAN}) :CAN baud rate clock





2.8 A/D Converter

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD = EVDD = 3.5 to 5.5V, AVREF0 = 4.0 to 5.5V, VSS = EVSS = AVSS = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	(A),(A1)	AX. (A2)	Unit
Resolution						0 ,	bit
Overall error ^{Note1}		4.0V≤AVREF0<5.5V		±0.15	±0.3	±0.35	%FSR
Conversion time	tCONV		3.10		1	6	μs
Stabilization time	tSTA	After ADA0PS bit = 0 -> 1	2				μs
Recovery time for power down mode	tDPU		1				μs
Zero-scale error ^{Note1}	ZSE				±0.3	±0.35	%FSR
Full-scale error ^{Note1}	FSE				±0.3	±0.35	%FSR
Integral non-liniearity error Note2	INL				±2	2.5	LSB
Differential non-liniearity error Note2	DNL				±′	1.5	LSB
Analog input voltage	VIAN		AVSS		AVF	REF0	V
Analog input equivalent circuit capacitance Note3,4	CINA				6.	19	pF
Analog input equivalent circuit resistance Note3	RINA				2.	55	kΩ
AVREF0 current	IAREF0	A/D operating		4		7	mA
AVICE O CUITEIR	IAINEFU	A/D operation stop		1	1	0	μΑ
Conversion rusult when using		AVREF0 conversion	3FC		31	FF	HEX
Diagnostic function		AVSS conversion	000		00	03	HEX

Notes: 1. Overall error excluding quantization error (±0.05%FSE). It is indicated as a ratio to the fullscale value.

- Excluding quantization error (±1/2 LSB)
 Reference value. Not tested in production.
- 4. Does not include input/output capacitance CIO



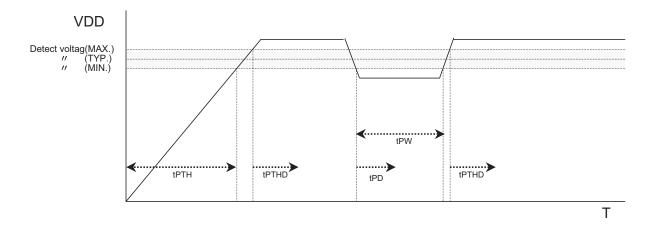
2.9 POC

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7 μ F, VDD = EVDD, VSS = EVSS = AVSS = 0V)

- ,		- /				
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detect voltage	VPOC0		3.3	3.5	3.7	V
Supply voltage rise time	tPTH	From VDD=0V to VDD=3.3V	0.002			ms
Response time1 Note1	tPTHD	In case of power on. After VDD reaches 3.7V.			2.0	ms
Response time2 Note2	tPD	In case of power off. After VDD drop 3.3V.		0.2	1.0	ms
VDD minimum width	tPW		0.2			ms

Notes: 1. From detect voltage to release reset signal

2. From detect voltage to occurrence of reset signal



Note: POC is available only in M2 devices. Refer to 'Ordering information' in the V850ES/Fx3-L User'sManual.



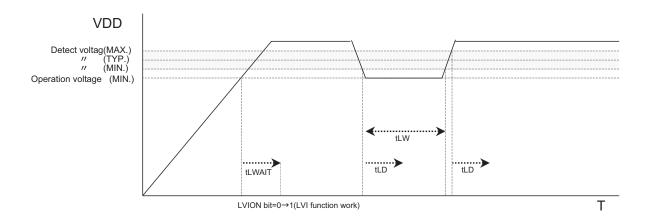
2.10 LVI

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detect voltage	VLVI0		3.8	4.0	4.2	V
Detect voltage	VLVI1		3.5	3.7	3.9	V
Response time Note1	tLD	After VDD reaches VLVI0/1(max). After VDD drop VLVI0/1(min).		0.2	2.0	ms
VDD minimum width	tLW		0.2			ms
Reference voltage stabilization wait time Note2	tLWAIT	After VDD reaches 3.3V. After LVION bit (LVIM.bit7) = 0->1		0.1	0.2	ms

Notes: 1. From detect voltage to occurrence interrupt/reset signal

2. If POC functionality is available, the wait time is not needed.

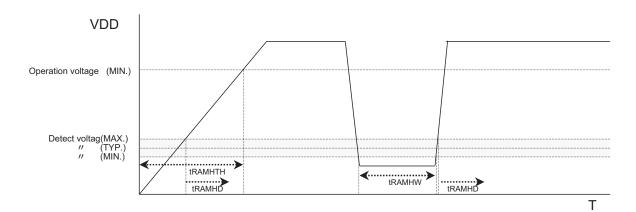


2.11 RAM Retention Flag

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7 μ F, VDD = EVDD = 1.9 to 5.5 ν F, VSS = EVSS = AVSS = 0 ν F)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detect voltage	VRAMH		1.9	2.0	2.1	V
Supply voltage rise time	tRAMHTH	From VDD=0V to VDD=3.3V	0.002		1800	ms
Response time Note1	tRAMHD	After VDD reaches 2.1V.		0.2	2.0	ms
VDD minimum width	tRAMHW		0.2			ms

Notes: 1. From detect voltage to set RAMFbit (RAMS.bit0)



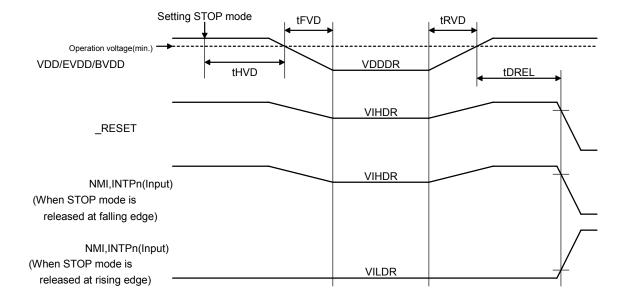


2.12 Data Retention Characteristics

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD = EVDD = 1.9 to 5.5V, VSS = EVSS = AVSS = 0V) (

,	,					
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention power supply voltage	VDDDR	STOP mode (All function is stopped)	1.9		5.5	V
Data retention power supply current	IDDDR	VDDDR=2.0V(All function is stopped)		6.5	70	μΑ
Supply voltage rise time	tRVD		1			μs
Supply voltage fall time	tFVD		1			μs
Supply voltage hold time	tHVD	After STOP mode	0			ms
STOP release signal input time	tDREL	After VDD reaches operating voltage range MIN. 3.3V	0			ms
Data retention high-level input voltage	VIHDR	All input port	0.9-VDDDR		VDDDR	٧
Data retention low-level input voltage	VILDR	All input port	0		0.1-VDDDR	٧

Remark: When STOP mode is entered/released operation voltage range must be controlled.





2.13 Flash Memory Programming Characteristics

(a) Basic Characteristics

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7 μ F, VDD = EVDD, AVREF0 = 3.5 to 5.5 ν F, VSS = EVSS = AVSS = 0 ν F)

Parameter	Symbol	Conditions	MIN.	TYP.		MAX.	1	Unit
1 didiliotoi	Cymbol	Gorraldono	IVIII V.		(A)	(A1)	(A2)	Orne
Operation frequency	fCPU		4		20			MHz
Supply voltage	VDD		3.3			5.5		V
Number of rewrites	CWRT	Code Flash			1000			count
High level input voltage	VIH	FLMD0	0.8-EVDD			EVDD		V
Low level input voltage	VIL	FLMD0	EVSS		0	.2·EVD	D	V
Programming temperature	tPRG		-40		+85	+110	+125	°C
Data retention		Code Flash	15					year

Remark: The initial write when the product is shipped, any erase → write set of operations, or any programming operation is counted as one rewrite.

Example: P: Program(write) E: Erase

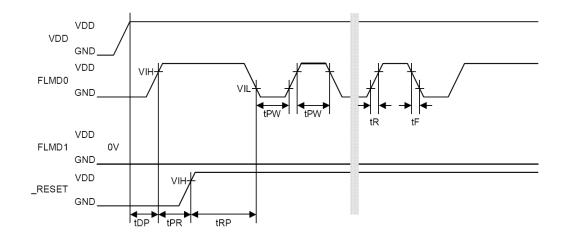
Product is shipped \rightarrow P \rightarrow E \rightarrow P \rightarrow E \rightarrow P : Rewrite count: 3 Product is shipped \rightarrow E \rightarrow P \rightarrow E \rightarrow P \rightarrow E \rightarrow P : Rewrite count: 3

(b) Serial Writing Operation Characteristics

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade,

C=4.7uF, VDD = EVDD, AVREF0 = 3.5 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
FLMD0 setup time (from VDD)	tDP		1			ms
RESET release (from FLMD0)	tPR		2			ms
FLMD0 pulse input start (from raise edge of _RESET)	tRP		800			μs
FLMD0 high level width / low level width	tPW		10		100	μs
FLMD0 raise time	tR				50	ns
FLMD0 fall time	tF				50	ns

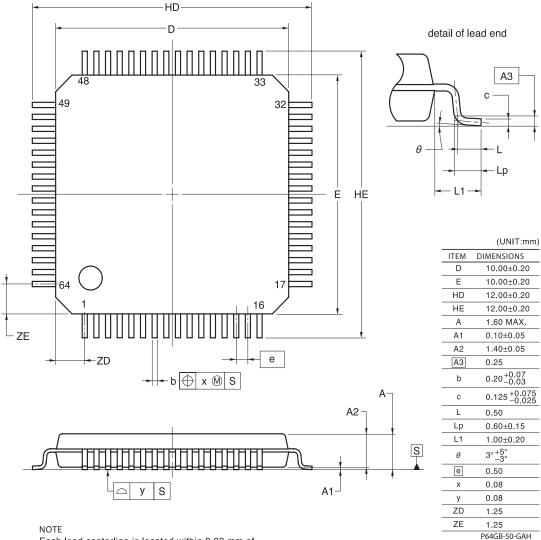




3. Package

3.1 Package Dimension

64-PIN PLASTIC LQFP(FINE PITCH)(10x10)

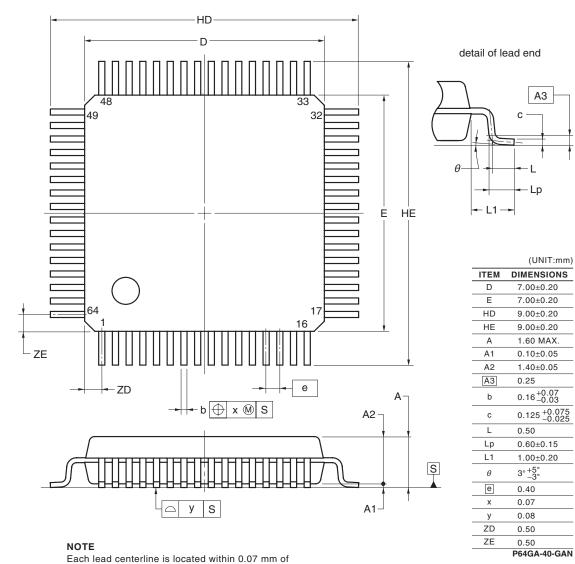


Each lead centerline is located within 0.08 mm of its true position at maximum material condition.



64-PIN PLASTIC LQFP (FINE PITCH) (7x7)

its true position at maximum material condition.

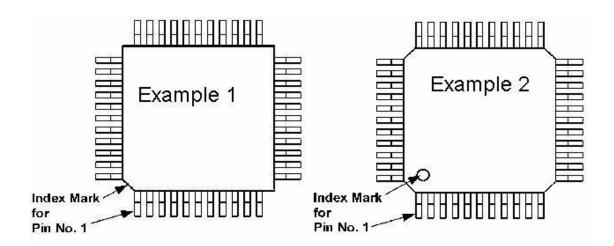


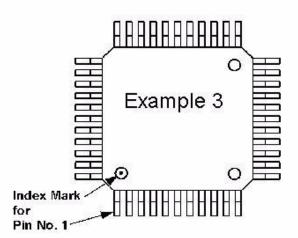
Datasheet U19190EE1V0DS00



3.2 Product Marking

3.2.1 Marking of pin 1 at a QFP (Quad Flat Package)





Example 1: The index mark for pin 1 is the beveled edge of the package

Example 2: The index mark for pin 1 is a round notch at one of the 4 edges. In this case, the shape of all edges is identical (usually beveled).

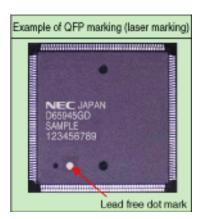
Example 3: For production reasons, two or more similar notches may be located at the top of the package. In such a case the index marker for pin 1 is a round notch with an additional mark in it.

Note: RoHS compliant devices have an additional dot at the top side. Do not mix it up with the marking for pin 1. For details see 3.2.2 "Identification of Lead-Free Products" on page 35.



3.2.2 Identification of Lead-Free Products

Lead-Free products are marked with a dot "•". The marking methods are the paint or the laser (It doesn't sink in). The shape of lead-free marks is a circle. Example:



V850ES/FE3-L

4. Change History

Version	Chapter	Comment
V1.0		Initial release



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